

David C Ingram

List of Publications by Year in descending order

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95
papers

2,007
citations

279778

23
h-index

276858

41
g-index

97
all docs

97
docs citations

97
times ranked

1631
citing authors

#	ARTICLE	IF	CITATIONS
1	Cold field emission from CVD diamond films observed in emission electron microscopy. Electronics Letters, 1991, 27, 1459.	1.0	387
2	Metal/semiconductor phase transition in chromium nitride(001) grown by rf-plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2004, 85, 6371-6373.	3.3	108
3	Molecular beam epitaxy control of the structural, optical, and electronic properties of ScN(001). Journal of Applied Physics, 2001, 90, 1809-1816.	2.5	105
4	Crystalline phase and orientation control of manganese nitride grown on MgO(001) by molecular beam epitaxy. Journal of Applied Physics, 2002, 91, 1053-1059.	2.5	88
5	ScGaN alloy growth by molecular beam epitaxy: Evidence for a metastable layered hexagonal phase. Physical Review B, 2004, 70, .	3.2	74
6	Reconstruction Control of Magnetic Properties during Epitaxial Growth of Ferromagnetic Mn ₃ Wurtzite GaN(0001). Physical Review Letters, 2006, 97, 146101.	7.8	57
7	Effects of coal syngas and H ₂ S on the performance of solid oxide fuel cells. Journal of Power Sources, 2007, 164, 659-667.	7.8	44
8	Effect of substrate bias on the properties of diamondlike carbon films deposited using unbalanced magnetron sputtering. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 2856-2862.	2.1	43
9	Phase stability, nitrogen vacancies, growth mode, and surface structure of ScN(001) under Sc-rich conditions. Journal of Crystal Growth, 2002, 242, 345-354.	1.5	42
10	The effect of MeV ion irradiation on the hydrogen content and resistivity of direct ion beam deposited diamondlike carbon. Nuclear Instruments & Methods in Physics Research B, 1988, 34, 68-73.	1.4	41
11	Ga/N flux ratio influence on Mn incorporation, surface morphology, and lattice polarity during radio frequency molecular beam epitaxy of (Ga,Mn)N. Journal of Applied Physics, 2003, 93, 5274-5281.	2.5	41
12	Composition-dependent structural properties in ScGaN alloy films: A combined experimental and theoretical study. Journal of Applied Physics, 2005, 98, 123501.	2.5	36
13	Hydrogen analysis as a function of depth for hydrogenous films and polymers by proton recoil detection. Nuclear Instruments & Methods in Physics Research B, 1985, 6, 430-434.	1.4	35
14	Ellipsometric measurements of molecular beam epitaxy grown semiconductor multilayer thicknesses: A comparative study. Journal of Applied Physics, 1987, 62, 4867-4871.	2.5	32
15	Applications of MeV ion beams to material processing. Nuclear Instruments & Methods in Physics Research B, 1985, 12, 161-169.	1.4	31
16	A study of thin films of V ₂ O ₅ containing molybdenum from an evaporation boat. Thin Solid Films, 2004, 460, 30-35.	1.8	31
17	SiN _x :Tb ³⁺ Yb ³⁺ , an efficient down-conversion layer compatible with a silicon solar cell process. Solar Energy Materials and Solar Cells, 2016, 145, 84-92.	6.2	31
18	Fe/Rh (100) multilayer magnetism probed by x-ray magnetic circular dichroism. Physical Review B, 1997, 56, 5474-5483.	3.2	28

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19	A Systematic Study of Plasma Activation of Silicon Surfaces for Self Assembly. ACS Applied Materials & Interfaces, 2015, 7, 25024-25031.	8.0	28
20	Structural and magnetic phase transitions in chromium nitride thin films grown by rf nitrogen plasma molecular beam epitaxy. Physical Review B, 2017, 96, .	3.2	28
21	An investigation of growth mechanism of coal derived graphene films. Materials Today Communications, 2017, 11, 147-155.	1.9	27
22	Mass density and hydrogen concentration in "diamond-like" carbon films: Proton recoil, Rutherford backscattering and ellipsometric analysis. Thin Solid Films, 1986, 137, 225-230.	1.8	25
23	Molecular beam epitaxial growth of zinc-blende FeN(111) on wurtzite GaN(0001). Journal of Alloys and Compounds, 2008, 463, 257-262.	5.5	25
24	Range distributions of MeV implants in silicon. Nuclear Instruments & Methods in Physics Research B, 1985, 7-8, 361-365.	1.4	24
25	Damage annealing behavior of 3 MeV Si+ implanted silicon. Applied Physics Letters, 1987, 51, 172-174.	3.3	24
26	Range distributions of MeV implants in silicon II. Nuclear Instruments & Methods in Physics Research B, 1987, 21, 460-465.	1.4	24
27	Hydrogen Evolution Reaction Kinetics on Electrodeposited Pt-M (M = Ir, Ru, Rh, and Ni) Cathodes for Ammonia Electrolysis. Journal of the Electrochemical Society, 2014, 161, E12-E22.	2.9	23
28	Properties of amorphous GaN _x prepared by ion beam assisted deposition at room temperature. Journal of Applied Physics, 2003, 93, 3954-3962.	2.5	22
29	MeV Si implantation in GaAs. Nuclear Instruments & Methods in Physics Research B, 1985, 6, 287-291.	1.4	18
30	Thin-film hermeticity: A quantitative analysis of diamondlike carbon using variable angle spectroscopic ellipsometry. Journal of Applied Physics, 1988, 64, 4175-4180.	2.5	18
31	Epitaxial growth of ferromagnetic -phase manganese gallium on semiconducting scandium nitride (001). Journal of Crystal Growth, 2009, 311, 2265-2268.	1.5	18
32	Optical and interfacial electronic properties of diamond-like carbon films. Thin Solid Films, 1984, 119, 121-126.	1.8	17
33	Roughness studies of ion beam processed molybdenum surfaces. Journal of Applied Physics, 1986, 59, 257-262.	2.5	17
34	Diamond-infiltrated carbon-carbon composites. Diamond and Related Materials, 1993, 2, 1069-1077.	3.9	17
35	Optical properties of ion-beam-deposited ion-modified diamondlike (a-C:H) carbon. Journal of Applied Physics, 1988, 64, 2611-2616.	2.5	16
36	Space charge limited current, variable range hopping and mobility gap in thermally evaporated amorphous InSe thin films. Journal of Materials Science: Materials in Electronics, 2004, 15, 787-792.	2.2	16

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37	The Edwards Accelerator Laboratory at Ohio University. <i>Physics Procedia</i> , 2017, 90, 448-454.	1.2	16
38	Heteroepitaxial growth and surface structure of L1-MnGa(111) ultra-thin films on GaN(0001). <i>Applied Physics Letters</i> , 2013, 103, .	3.3	15
39	Absolute cross section for forward recoiling hydrogen with 1.0–12.5 MeV 4He. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2003, 211, 305-311.	1.4	14
40	Optical conductivity tuning and electrical properties of a-Be x Zn y O thin films. <i>Journal of Non-Crystalline Solids</i> , 2016, 440, 31-37.	3.1	14
41	Successive Surface Reactions on Hydrophilic Silica for Modified Magnetic Nanoparticle Attachment Probed by Sum-Frequency Generation Spectroscopy. <i>Langmuir</i> , 2018, 34, 12680-12693.	3.5	14
42	Thermal oxidation of silicon in a residual oxygen atmosphere—the RESOX process—for self-limiting growth of thin silicon dioxide films. <i>Semiconductor Science and Technology</i> , 2016, 31, 105007.	2.0	13
43	Structure and magnetism in Ga-rich MnGa/GaN thin films and unexpected giant perpendicular anisotropy in the ultra-thin film limit. <i>Applied Surface Science</i> , 2016, 367, 312-319.	6.1	13
44	The nitrogen concentration effect on Ce doped SiO _x N _y emission: towards optimized Ce ³⁺ for LED applications. <i>Nanoscale</i> , 2018, 10, 3823-3837.	5.6	13
45	Study of Mo, Au, and Ni implanted molybdenum laser mirrors by multiple angle of incidence spectroscopic ellipsometry. <i>Journal of Applied Physics</i> , 1986, 60, 779-788.	2.5	12
46	Contribution from Ising domains overlapping out-of-plane to perpendicular magnetic anisotropy in Mn ₄ N thin films on MgO(001). <i>Journal of Magnetism and Magnetic Materials</i> , 2017, 439, 236-244.	2.3	12
47	Atomic and carrier profiles of 1, 2, 4, and 6 MeV B ³⁰ Si implanted into GaAs. <i>Journal of Applied Physics</i> , 1989, 65, 2986-2990.	2.5	11
48	The effect of ultrasonic pre-treatment on nucleation density of chemical vapor deposition diamond. <i>Journal of Applied Physics</i> , 1995, 78, 5745-5749.	2.5	11
49	Room temperature ferromagnetism in CrGa _N : Dependence on growth conditions in rf N-plasma molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2005, 285, 300-311.	1.5	11
50	Structural and magnetic properties of ferrimagnetic μ -phase Mn ₄ N and antiferromagnetic η -phase Mn ₁₀ N thin films on MgO(001). <i>Journal of Crystal Growth</i> , 2016, 446, 60-67.	1.5	11
51	Measured response of bubble neutron detectors and prospects for alpha knock-on diagnostics. <i>Review of Scientific Instruments</i> , 2001, 72, 796-800.	1.3	10
52	Growth and optical properties of amorphous Be _{0.13} Zn _{0.38} O _{0.49} thin films prepared by radio frequency magnetron sputtering. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 2783-2786.	3.1	10
53	Effect of bias and hydrogenation on the elemental concentration and the thermal stability of amorphous thin carbon films, deposited on Si substrate. <i>Diamond and Related Materials</i> , 2009, 18, 1333-1337.	3.9	10
54	Ion beam induced adhesion of copper films on molybdenum. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1986, 13, 462-466.	1.4	9

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55	Amorphous carbon nitride for high temperature capacitor dielectric. <i>Diamond and Related Materials</i> , 2006, 15, 259-263.	3.9	9
56	Optical properties, luminescence quenching mechanism and radiation hardness of Eu-doped GaN red powder phosphor. <i>Radiation Measurements</i> , 2010, 45, 500-502.	1.4	9
57	Improved thermal stability and narrowed line width of photoluminescence from InGaN nanorod by ytterbium doping. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 413-417.	0.8	9
58	Surface structures of L10-MnGa (001) by scanning tunneling microscopy and first-principles theory. <i>Applied Surface Science</i> , 2017, 422, 985-989.	6.1	9
59	High dose implantation of xenon into nickel. <i>Nuclear Instruments & Methods in Physics Research</i> , 1982, 194, 117-119.	0.9	8
60	Trapping of hydrogen in diamond. <i>Diamond and Related Materials</i> , 1993, 2, 1414-1419.	3.9	8
61	On the difficulties in interpreting thermal evolution spectra. <i>Vacuum</i> , 1979, 29, 303-307.	3.5	7
62	Damage profiles of MeV implants of Ga and Si in silicon. <i>Nuclear Instruments & Methods in Physics Research B</i> , 1987, 21, 466-470.	1.4	7
63	Removal of non-diamond carbon from the surface of CVD diamond films. <i>Diamond and Related Materials</i> , 1994, 3, 1227-1229.	3.9	7
64	Growth and study of Tb ³⁺ doped Nb ₂ O ₅ thin films by radiofrequency magnetron sputtering: Photoluminescence properties. <i>Applied Surface Science</i> , 2022, 597, 153711.	6.1	7
65	The Implantation Of MeV Er Into Si. <i>Proceedings of SPIE</i> , 1985, , .	0.8	6
66	Ion beam smoothing of metallic mirrors. <i>Materials Science and Engineering</i> , 1987, 90, 417-421.	0.1	6
67	Quantum-efficiency measurements on carbon-hydrogen-alloy-based solar cells. <i>Solar Energy Materials and Solar Cells</i> , 1998, 51, 433-440.	6.2	6
68	Magnetostrictive iron gallium thin films grown onto antiferromagnetic manganese nitride: Structure and magnetism. <i>Applied Physics Letters</i> , 2016, 109, 142402.	3.3	6
69	Thermal evolution of gas from a solid following detrapping and diffusion during a linear tempering schedule. <i>Vacuum</i> , 1978, 28, 69-72.	3.5	5
70	Atomic Profiles of High Energy (MeV) Si Implanted into GaAs. <i>Materials Research Society Symposia Proceedings</i> , 1987, 93, 73.	0.1	5
71	Measurements of the differential cross-section on thick and thin targets. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2013, 305, 45-50.	1.4	4
72	A low energy ion beam system for thermal evolution measurements of damage in ion bombarded single crystals. <i>Vacuum</i> , 1984, 34, 239-244.	3.5	3

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73	Growth of Carbon-Nitrogen Films with a Broad Beam RF Ion Source. Materials Research Society Symposia Proceedings, 2001, 693, 382.	0.1	3
74	RBS ion channeling study of low concentrations of ion implanted samarium in GaN. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 699-702.	1.4	3
75	Influence of Ni concentration on the crystallization of amorphous Si films and on the development of different Ni-silicide phases. Journal of Applied Physics, 2014, 116, 123508.	2.5	3
76	Effect of radiation-induced defects on the superfluid density and optical conductivity of overdoped $\text{LaSr}_x\text{CuO}_4$. Physical Review B, 2022, 105, .	3.2	3
77	MeV Implantation Of N-Type Dopants Into GaAs. Proceedings of SPIE, 1985, 0530, 35.	0.8	2
78	Diamondlike Carbon For Infrared Optics. Proceedings of SPIE, 1989, , .	0.8	2
79	Reusable Chemically Micropatterned Substrates via Sequential Photoinitiated Thiol-Ene Reactions as a Template for Perovskite Thin-Film Microarrays. ACS Applied Electronic Materials, 2019, 1, 2279-2286.	4.3	2
80	Mixing Rocksalt and Wurtzite Structure Binary Nitrides to Form Novel Ternary Alloys: ScGaN and MnGaN. Materials Research Society Symposia Proceedings, 2003, 799, 339.	0.1	1
81	Thermal Stability of Thin Films of Ion Beam Deposited CN _x . Materials Research Society Symposia Proceedings, 2003, 792, 568.	0.1	1
82	Publisher's Note: ScGaN alloy growth by molecular beam epitaxy: Evidence for a metastable layered hexagonal phase [Phys. Rev. B70, 193309 (2004)]. Physical Review B, 2004, 70, .	3.2	1
83	Comparing modern measurements of the $^{11}\text{B}(d,n)^{12}\text{C}$ excitation function with previous values. , 2013, , .		1
84	The Breakup Cross Section of the D+D Reaction at 6.94 MeV. EPJ Web of Conferences, 2016, 113, 08016.	0.3	1
85	Enhancing Blue Emission in Ce Doped Silicon Oxynitrides Based Electroluminescent Devices. ECS Journal of Solid State Science and Technology, 2019, 8, R157-R163.	1.8	1
86	Au and Pt Diffusion in Electrodeposited Amorphous Sb ₂ Te ₃ Thin Films. Physica Status Solidi (B): Basic Research, 2021, 258, 2000428.	1.5	1
87	Ion Beam Study of Early Stages of Growth of GaN films on Sapphire. Materials Research Society Symposia Proceedings, 2002, 743, L3.5.1.	0.1	0
88	Trapping of argon in ion beam deposited thin films of CN _x Hy. Materials Research Society Symposia Proceedings, 2003, 792, 574.	0.1	0
89	Trapping of Hydrogen in Carbon Nitride Films During or After High Temperature Heat Treatment. Materials Research Society Symposia Proceedings, 2004, 854, U8.4.1.	0.1	0
90	Measurement of deuterium in the presence of protium by elastic recoil spectroscopy. Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 450-454.	1.4	0

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91	Single vs. dual ion beam growth of CN/sub x/. , 2006, , .		0
92	Optical and Spectroscopic Ellipsometric Study of Indium Boron Nitride Sputtered Thin Films with Low Boron Concentration. Materials Research Society Symposia Proceedings, 2011, 1307, 1.	0.1	0
93	RBS Analysis of Down-conversion Layers Comprising Two Rare-Earth Elements. Physics Procedia, 2017, 90, 32-40.	1.2	0
94	Hydrogen Outgassing and Secondary Electron Reduction From Laser-Processed Stainless Steel Anodes* , 2017, , .		0
95	(Invited) Enhancing the Blue Emission in Ce Doped Silicon Oxynitrides Thin Films for Electroluminescence Device Applications. ECS Transactions, 2018, 85, 9-21.	0.5	0